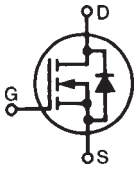
IXYS

Polar™ Power MOSFET

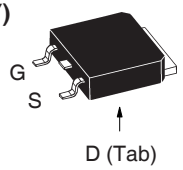
IXTY1N120P
IXTA1N120P
IXTP1N120P

V_{DSS} = 1200V
I_{D25} = 1A
$R_{DS(on)}$ ≤ 20Ω

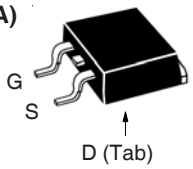
N-Channel Enhancement Mode
Avalanche Rated



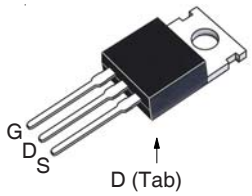
TO-252 (IXTY)



TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1200	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1200	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	1.0	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	1.8	A
I_A	T_C = 25°C	1.0	A
E_{AS}	T_C = 25°C	100	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	10	V/ns
P_D	T_C = 25°C	63	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in
Weight	TO-252	0.35	g
	TO-263	2.50	g
	TO-220	3.00	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	1200			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 50μA	2.5		4.5	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±50	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			5	μA
	T_J = 125°C			200	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Notes 1& 2		15.5	20.0	Ω

Features

- International Standard Packages
- Low Q_G
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Switch-Mode and Resonant-Mode Power Supplies
- AC and DC Motor Drives
- Discharge Circiuts in Lasers, Spark Igniters, RF Generators
- High Voltage Pulse Power Applications

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 30V, I_D = 0.5 • I_{D25}, Note 1	0.55	0.90		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		445		pF
C_{oss}			25		pF
C_{rss}			5.4		pF
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		17.6		nC
Q_{gs}			3.5		nC
Q_{gd}			10.6		nC
$t_{d(on)}$	**Resistive Switching Times**		20		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		28		ns
$t_{d(off)}$	R_G = 30Ω (External)		54		ns
t_f			27		ns
R_{thJC}				2.0	°C/W
R_{thCS}	TO-220		0.50		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			1	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			3	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 1A, -di/dt = 100A/μs, V_R = 100V		900		ns

Notes: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123B1 6,306,728B1 6,404,065B1 6,534,343 6,583,505 6,683,344 6,710,405B2 6,710,463 6,727,585 6,759,692 6,771,478B2 7,005,734B2 7,063,975B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25°C

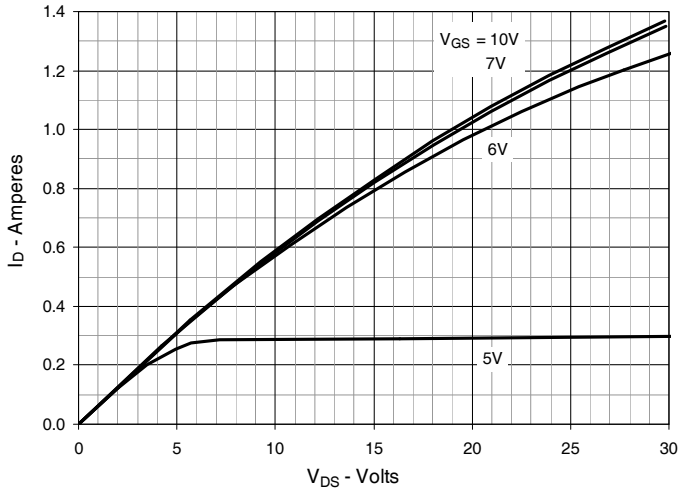


Fig. 2. Output Characteristics @ T_J = 125°C

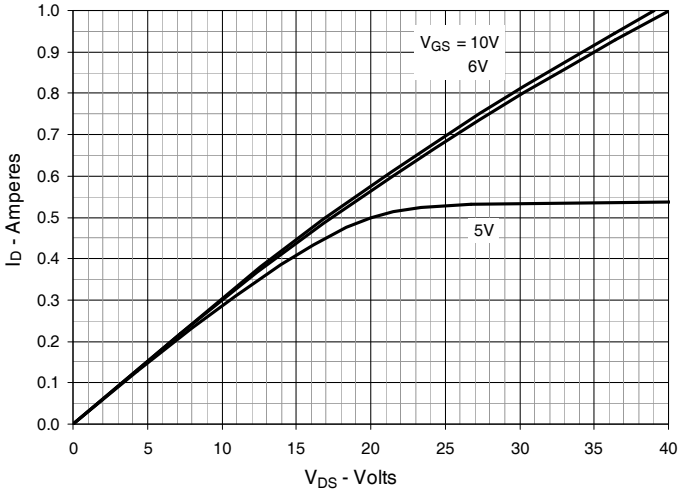


Fig. 3. $R_{DS(on)}$ Normalized to I_D = 0.5A Value vs. Junction Temperature

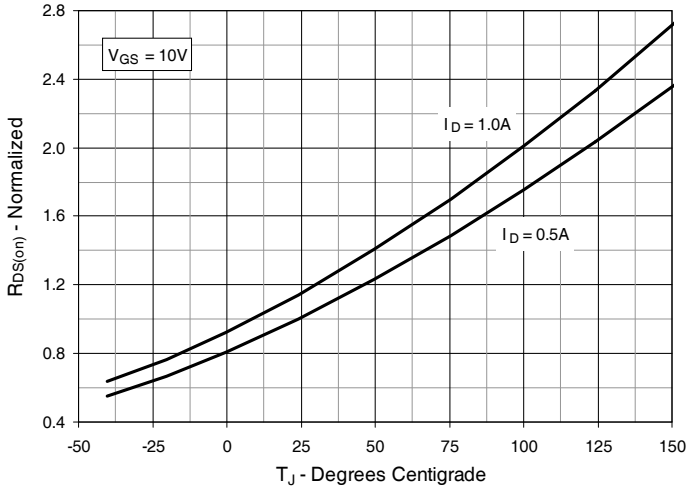


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 0.5A Value vs. Drain Current

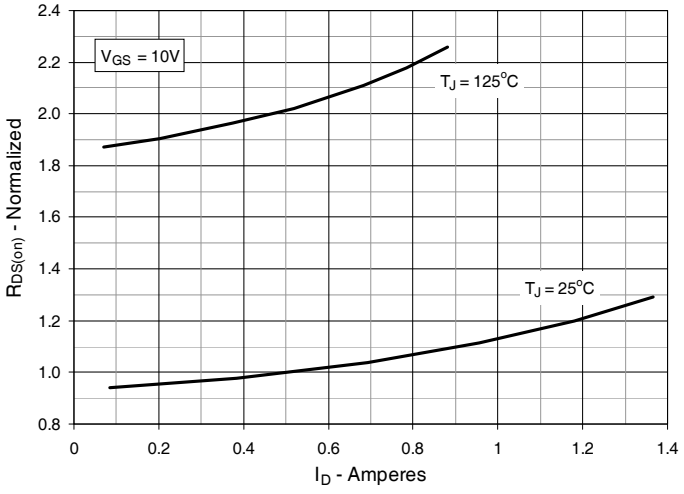


Fig. 5. Maximum Drain Current vs. Case Temperature

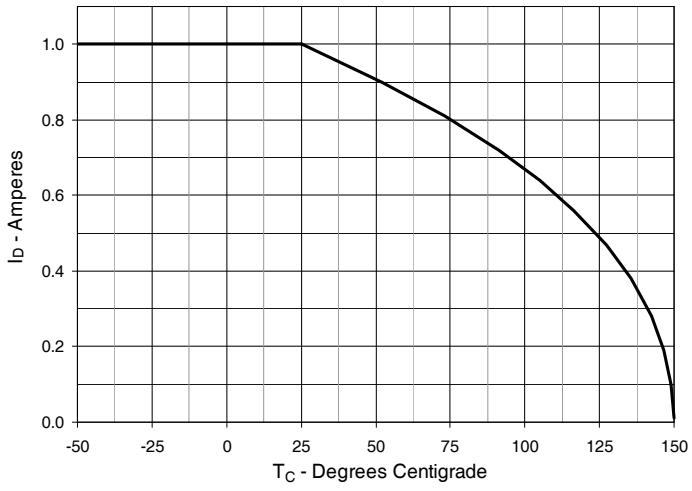
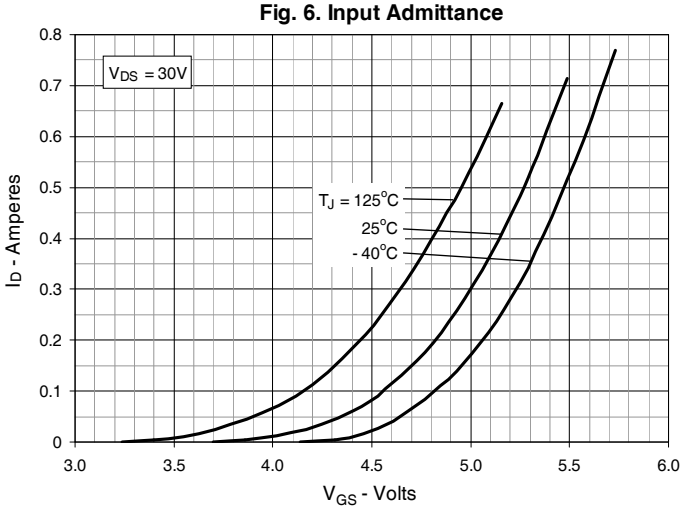


Fig. 6. Input Admittance



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Fig. 7. Transconductance

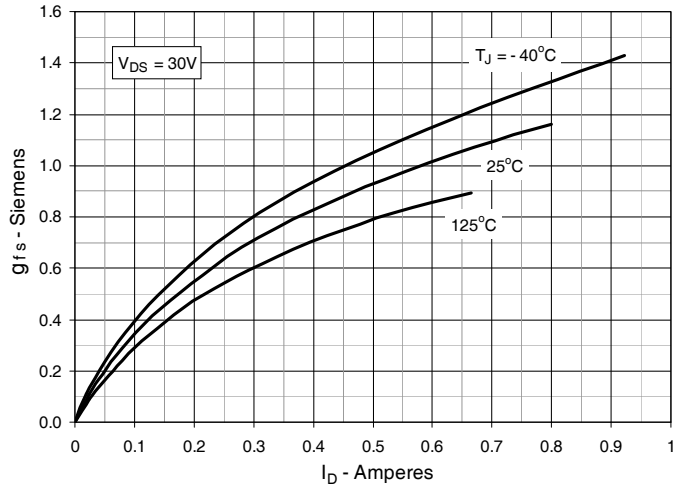


Fig. 8. Forward Voltage Drop of Intrinsic Diode

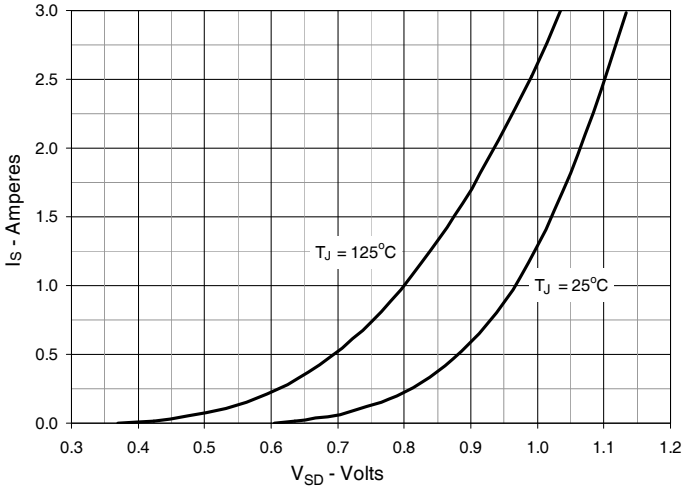


Fig. 9. Gate Charge

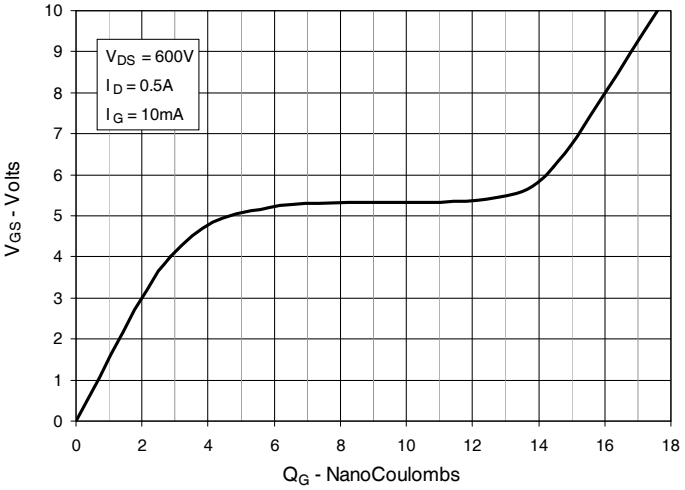


Fig. 10. Capacitance

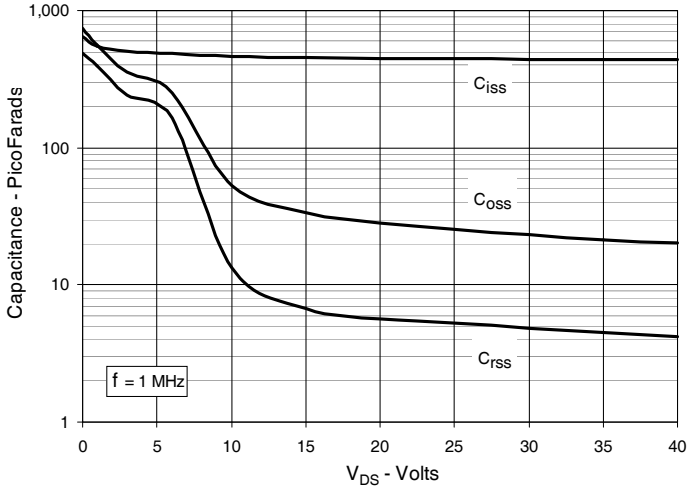
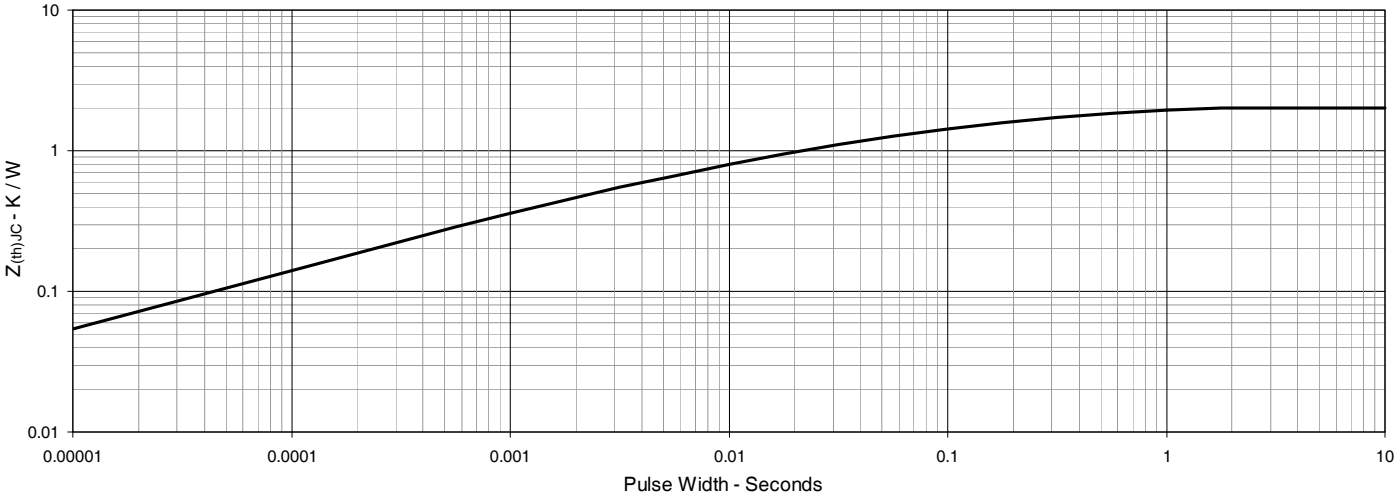
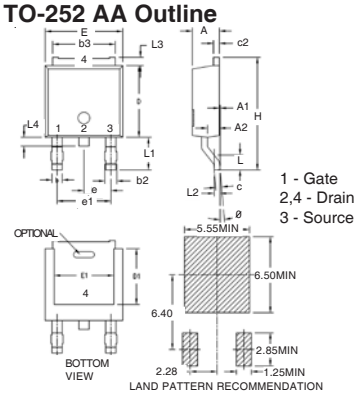


Fig. 11. Maximum Transient Thermal Impedance



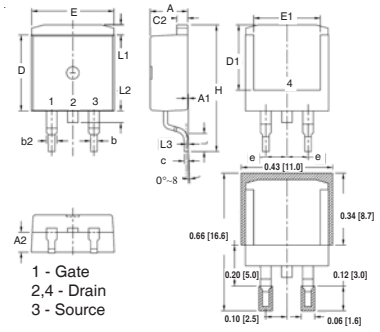
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TO-252 AA Outline



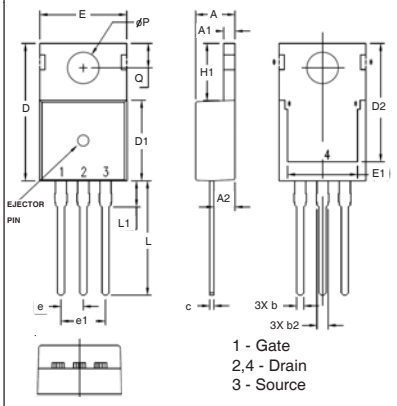
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.086	.094	2.19	2.38
A1	0	.005	0	0.12
A2	.038	.046	0.97	1.17
b	.025	.035	0.64	0.89
b2	.030	.045	0.76	1.14
b3	.200	.215	5.08	5.46
c	.018	.024	0.46	0.61
c2	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.180	.205	4.57	5.21
E	.250	.265	6.35	6.73
E1	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.055	.070	1.40	1.78
L1	.100	.115	2.54	2.92
L2	.020 BSC		0.50 BSC	
L3	.025	.040	0.64	1.02
L4	.025	.040	0.64	1.02
θ	0°	10°	0°	10°

TO-263 Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
e	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010 BSC		0.254 BSC	

TO-220 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

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